

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Hans-Joachim Müssig

Attorney Docket No.: 536-009.13 #2

Application No.: To be assigned

Group No.: To be assigned

Filed: Herewith

Examiner: To be assigned

For: SEMICONDUCTOR CAPACITOR AND MOSFET FITTED THEREWITH

Commissioner for Patents
Director of the U.S. Patent & Trademark Office
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Applicant submits herewith references of which they are aware, which they believe may be material to the examination of this application and in respect of which they may have a duty to disclose in accordance with 37 CFR 1.56.

While this Information Disclosure Statement may be "material" pursuant to 37 CFR 1.56, it is not intended to constitute an admission that any document referred to herein is "prior art" for this invention unless specifically designated as such.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined under 37 CFR 1.56(a) exists.

I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to:
Commissioner for Patents, P.O. Box 1450,
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Sue Muro

Jan. 4, 2005

Date

Attorney Docket No. 536-009.13
Serial No. (to be assigned)

This IDS is being submitted simultaneously with the request for entry into the U.S. national phase corresponding to PCT application number PCT/EP03/07179 having international filing date of July 4, 2003. Therefore, the undersigned respectfully submits that no fee is due for filing this IDS. Should any fees be due of which the undersigned is unaware, the Commissioner is hereby authorized to charge deposit account 23-0442 any fee deficiency required to submit this IDS.

A PTO-1449 with cited references is enclosed.

Respectfully submitted,


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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		ATTY DOCKET NO. 536-009.13	SERIAL NO. 10/520396 To be assigned
		APPLICANT: Hans Joachim Müssig	
		FILING DATE: Herewith	ART UNIT: To be assigned

UNITED STATES PATENT DOCUMENTS

EXAM. INITIAL		DOCUMENT NUMBER	ISSUE/PUBL DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	US	2002/0036313	3-28-2002	Sam Yang et al.			
	US	2003/0228747	12-11-2003	Kie Y. Ahn et al.			
	US	6,656,852	12-2-2003	Antonio Luis Pacheco Rotondaro et al.			
	US	2003/0119291	6-26-2003	Kie Y. Ahn			
	US	5,356,833	10-18-1994	Papu D. Maniar et al.			
	US	2003/0193061	10-16-2003	Hans-Jörg Osten			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	TRANSLATION YES/NO
	WO	02/097895	12-5-2002	Dietmar Krüger et al.			abstract only

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

	Surface Science 504 (2002) 159-166, XP-001189099, Initial stages of praseodymium oxide film formation on Si(001), H.-J. Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany; received 8 September 2001, accepted for publication 3 Dec. 2001.
	2001 IRW Final Report, 0-7803-7167-4/01/2001 IEEE, Can Praseodymium Oxide be an Alternative High-K Gate Dielectric Material for Silicon Integrated Circuits?, H. -J Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany.

Examiner

Date: